



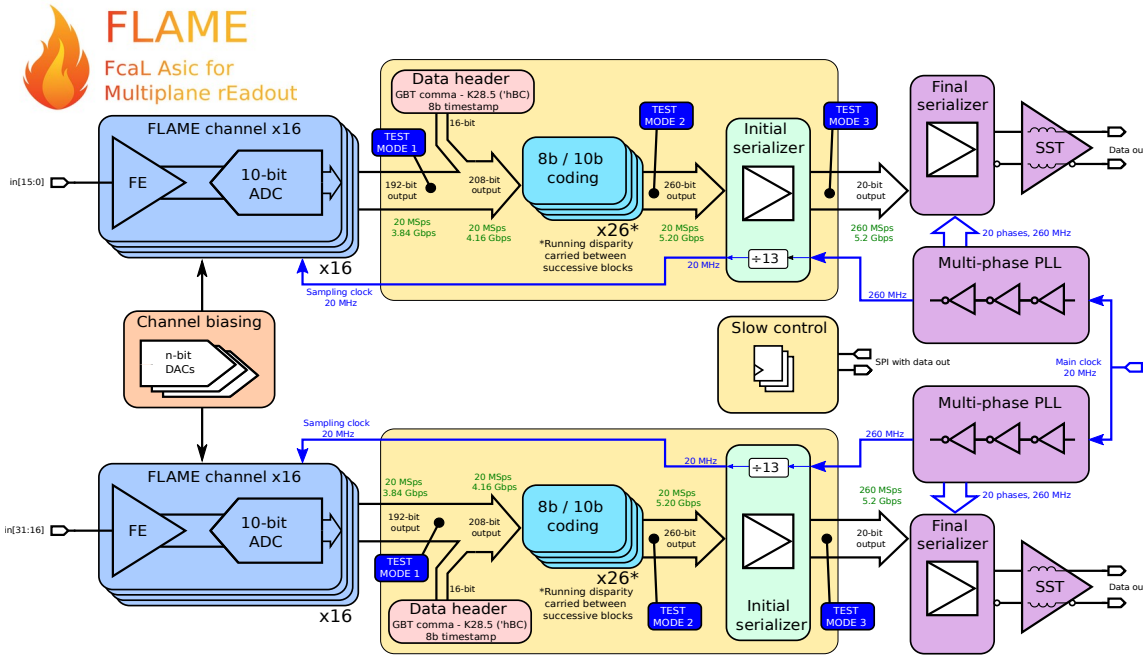
AGH UNIVERSITY OF SCIENCE  
AND TECHNOLOGY

# **Update from AGH activities in WP11.3 – CMOS 130/65 nm**

**Marek Idzik for AGH-UST**

- Activities in CMOS 130/65 nm
  - FLAME/FLAXE ASICs for calorimetry and LUXE experiment in CMOS 130nm
  - R&D on precise TAC-based TDC in CMOS 130nm
  - R&D on 10-bit ADC with internal threshold in CMOS 130nm
  - Publications about completed designs in CMOS 130/65 nm
  - Still waiting for man-power resources...
    - Fast Serializer&Transmitter in 130nm and 65nm
    - Test setups for ADCs in 130nm and 65nm

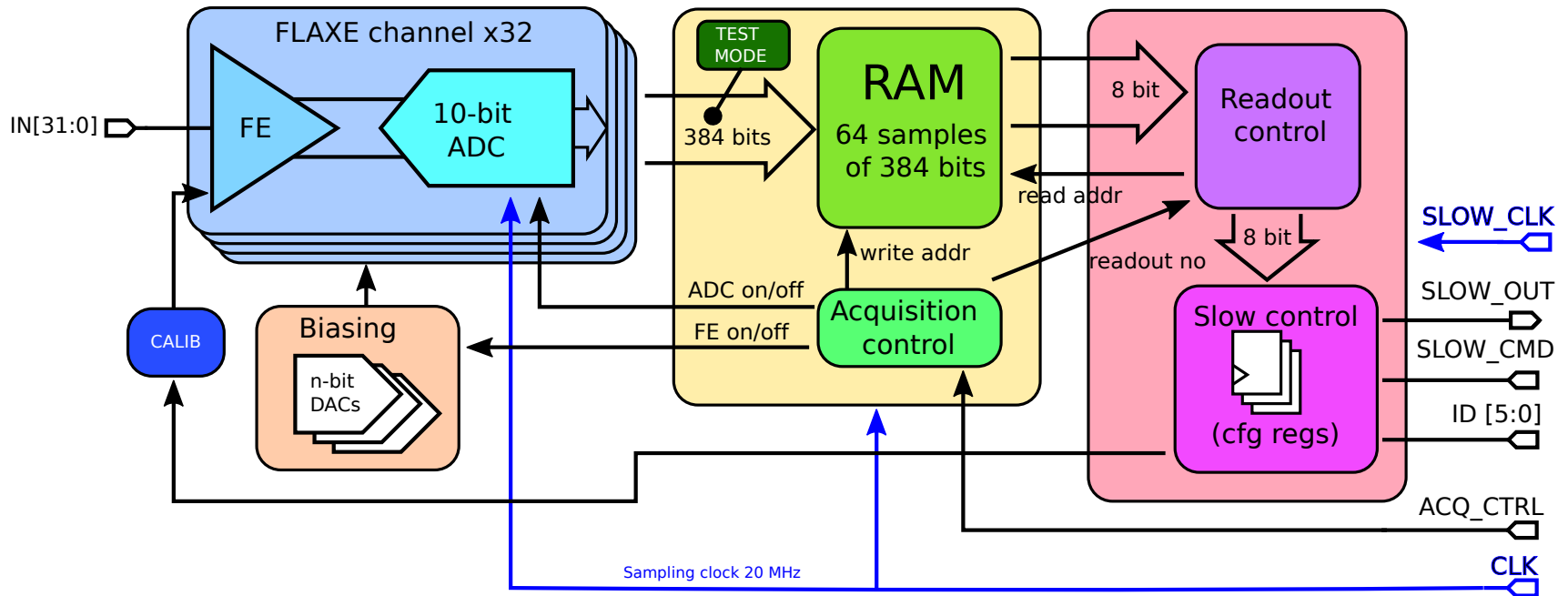
# Activities in CMOS 130nm FLAME ASIC for calorimetry



- 32-channel ASIC in CMOS 130nm
- In each channel
  - analog front-end ( $T_{peak} \sim 50\text{ns}$ , switched gain)
  - 10-bit ADC ( $f_{sample} = 20\text{MHz}$ )
- two fast 5.2 Gbps serializers and data transmitters

Presently FLAME chips are used for first LUXE test-beams. In the test-beam at DESY, 11-18 September 2022, a 4-chip front-end board (128 channels) was used to study the performance of Si and GaAs sensors and shower development. Analysis of the collected data are ongoing and publication is being prepared.

# Activities in CMOS 130nm FLAXE ASIC for ECAL-p in LUXE experiment

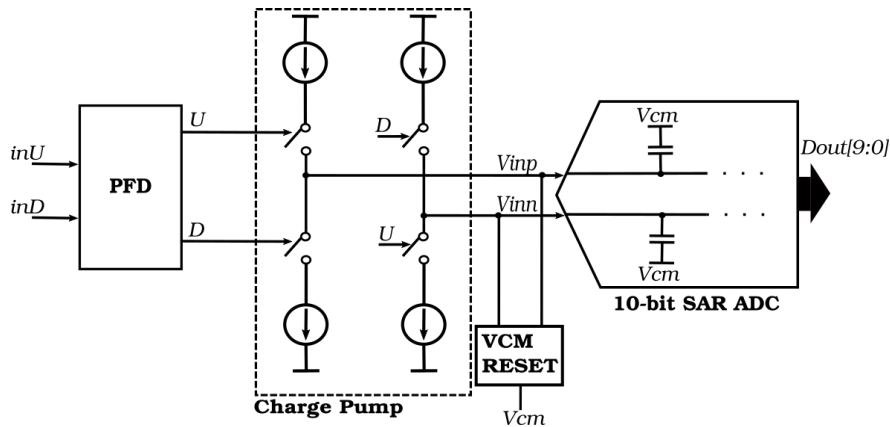


- FLAXE is a modified 32-channel FLAME in CMOS 130nm without high speed serialisers&transmitters – readout rate in LUXE ~10 Hz
- More than 1000 FLAXE chips were produced. Sent for dicing and packaging recently...

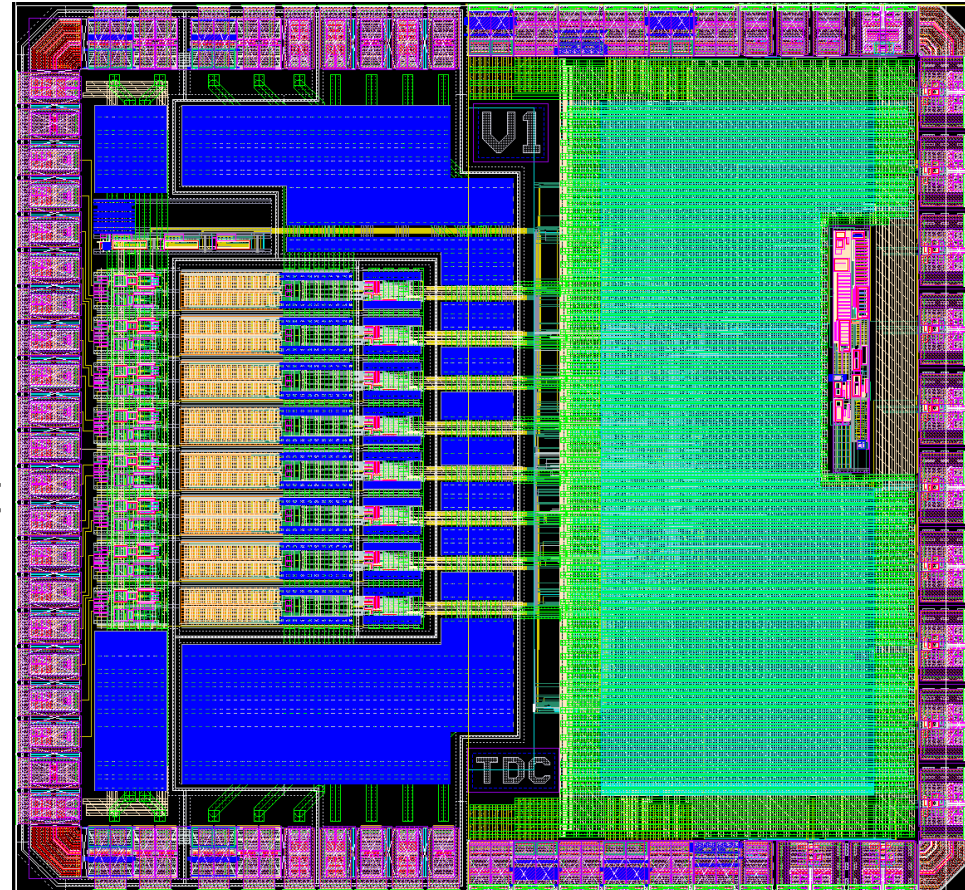
# Activities in CMOS 130nm

## R&D on precise TDC – TAC+ADC architecture

Single TDC channel



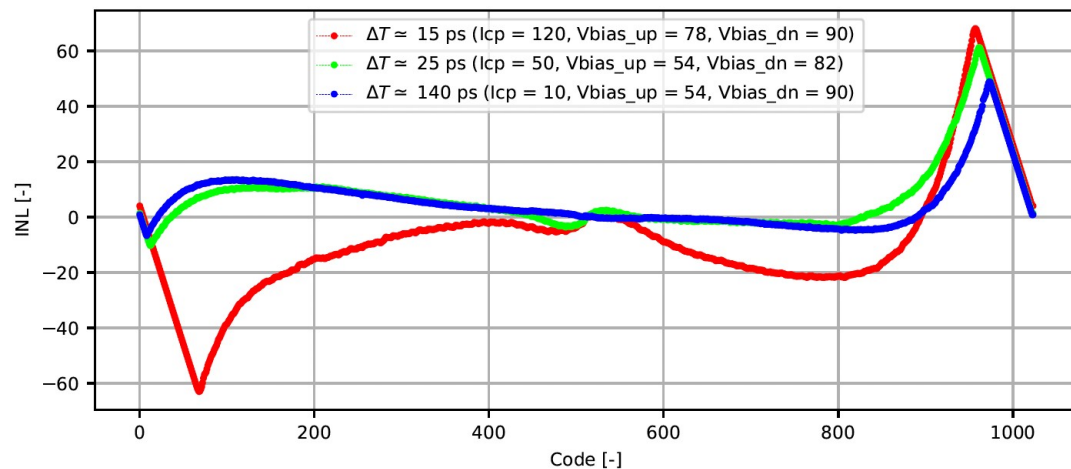
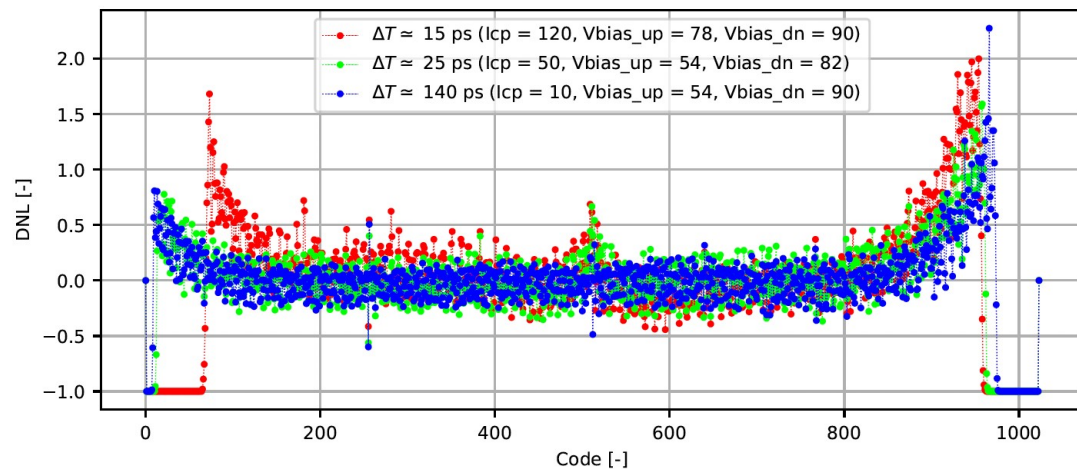
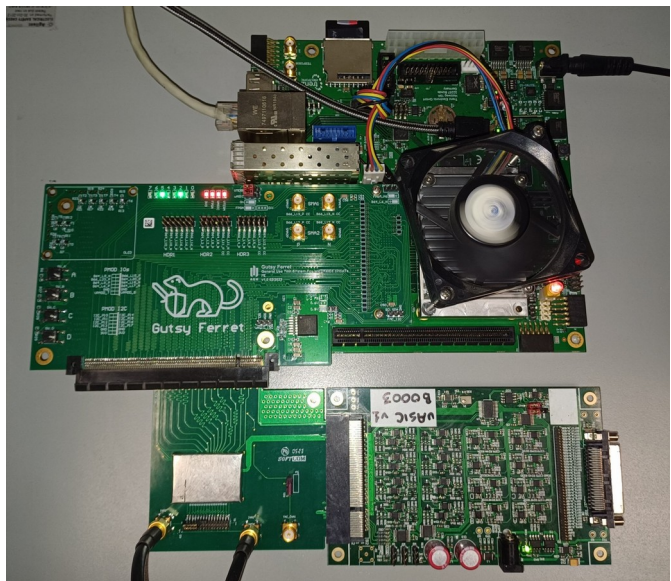
- New TAC-based TDC aiming at timing measurement precision of  $\sim 10ps$ , consuming  $\sim 1mW$
- As ADC the existing 10-bit SAR is used
- 8-channel prototype TDC chip was fabricated in 2022





# Activities in CMOS 130nm

## R&D on precise TDC - 1<sup>st</sup> measurements

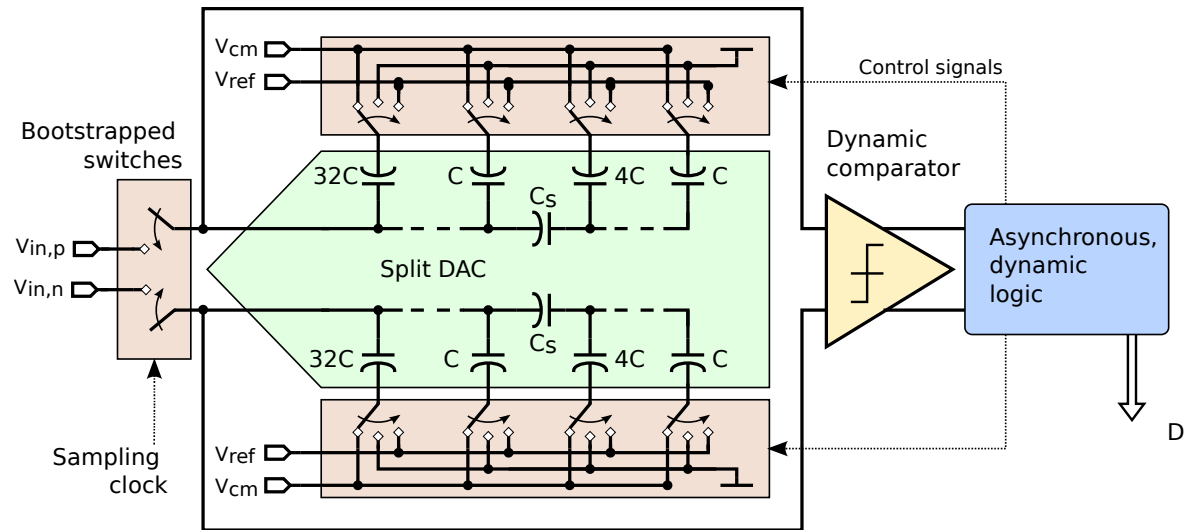


- TDC works!
- Good DNL < 1LSB
- INL rather high – to be understood
- Jitter < 1LSB

# Activities in CMOS 130nm R&D on 10-bit ADC with internal threshold

Our existing 10-bit ADC

- power 680uW@40MSps
- works up to 50MSps

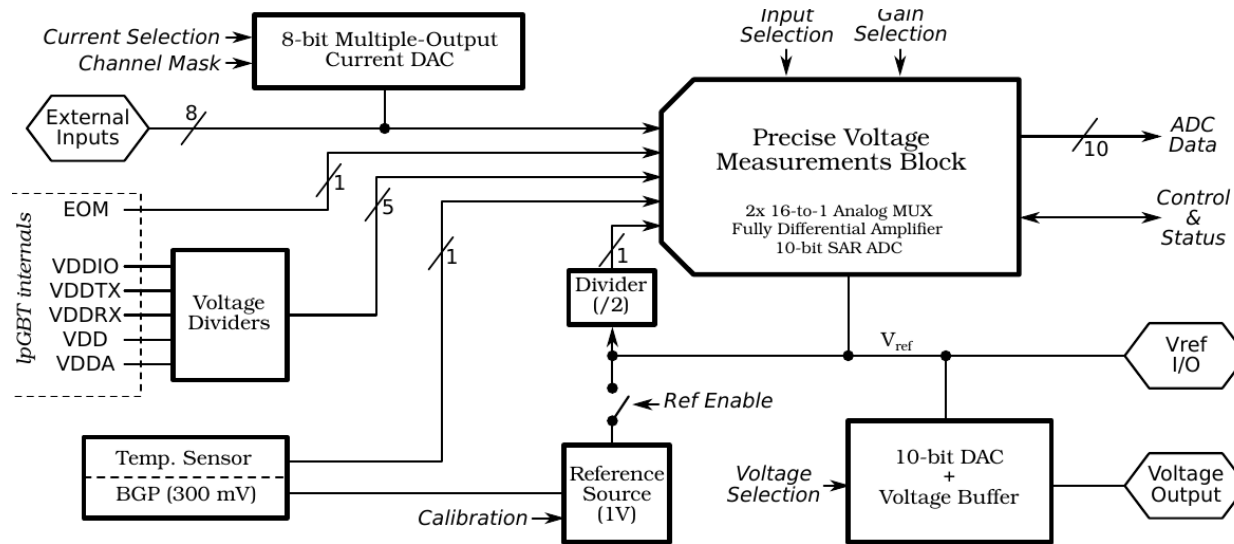


- To decrease power consumption even further, we are introducing additional comparison with threshold (MSc thesis)
  - If signal ( $>V_{th}$ ) - 11 comparisons are done instead of 10
  - If NO signal - 2 comparisons and ADC reset is done
- The result is that ADC is slightly slower
- Estimated power for low occupancy  $\sim$  one third of the current one
- Schematic done, layout in progress...

# Publications

## IpGBT monitoring system in CMOS 65nm

- **An IpGBT subsystem for environmental monitoring of experiments**, M. Firlej, T. Fiutowski, J. Fonseca, M. Idzik, S. Kulis, P. Moreira, J. Moroń, K. Świentek, Journal of Instrumentation 2023 vol. 18 art. no. P06008







## Publications

### 10-bit SAR ADCs in CMOS 130nm and 65nm

**An ultra-low power 10-bit, 50 MSps SAR ADC for multi-channel readout ASICs**, M. Firlej, T. Fiutowski, M. Idzik, S. Kulis, J. Moroń, K. Świentek, Journal of Instrumentation 2023 vol. 18 art. no. P11013

*This ADC in CMOS 130 nm is used in HGCR0C chip for HGCAL and TOFHIR chip for MTD, both for CMS Upgrade*

**Ultra-low power 10-bit 50-90 MSps SAR ADCs in 65 nm CMOS for multi-channel ASICs**, M. Firlej, T. Fiutowski, M. Idzik, J. Moroń, K. Świentek, Journal of Instrumentation 2024 vol. 19 art. no. P01029

*This ADC in CMOS 65 nm is used in lpGBT monitoring subsystem and is considered for MagnetStation and SciFi readout in LHCb Upgrade*

## Activities in TSMC 130/65 nm Still waiting for man-power resources...

- Serializers&Transmitters
  - prototype Serializer&Transmitter in CMOS 130nm ( $\sim 5\text{Gb/s}$ ) and CMOS 65nm ( $\sim 10\text{Gb/s}$ ) were designed and fabricated long time ago.
- ADCs
  - Prototype 12-bit SAR ADCs in CMOS 130nm and 65nm, and improved 10-bit SAR ADC in CMOS 65nm were designed and fabricate long time ago
  - Dedicated setup is partially done, PCB for tests are being designed...